

NPN SILICON TRIPLE DIFFUSED TRANSISTOR

DESCRIPTION

The 2SC3631-Z is designed for High Voltage Switching, especially in Hybrid Integrated Circuits.

FEATURES

- High Voltage $V_{CE0} = 400\text{ V}$
- High Speed $t_r < 0.7\ \mu\text{s}$
- Complement to 2SA1412-Z

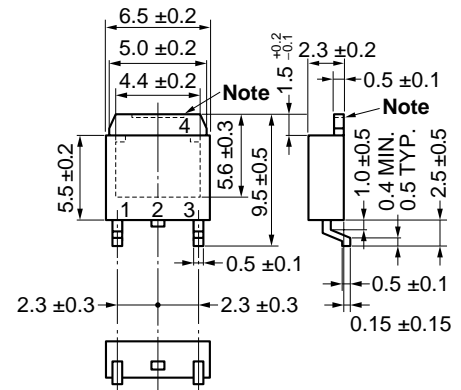
ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Collector to Base Voltage	V_{CBO}	500	V
Collector to Emitter Voltage	V_{CEO}	400	V
Emitter to Base Voltage	V_{EBO}	7	V
Collector Current (DC)	$I_{C(DC)}$	2.0	A
Collector Current (pulse) ^{Note 1}	$I_{C(pulse)}$	4.0	A
Total Power Dissipation ($T_A = 25^\circ\text{C}$) ^{Note 2}	P_T	2.0	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Notes 1. $PW \leq 10\text{ ms}$, Duty Cycle $\leq 50\%$

2. When mounted on ceramic substrate of $7.5\text{ cm}^2 \times 0.7\text{ mm}$

<R> PACKAGE DRAWING (Unit: mm)



TO-252 (MP-3Z)

1. Base
2. Collector
3. Emitter
4. Collector Fin

Note The depth of notch at the top of the fin is from 0 to 0.2 mm.

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ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	I _{CBO}			10	μA	V _{CB} = 400 V, I _E = 0
Emitter Cutoff Current	I _{EB0}			10	μA	V _{EB} = 5.0 V, I _C = 0
DC Current Gain	h _{FE1} *	40	60	120		V _{CE} = 5.0 V, I _C = 100 mA
DC Current Gain	h _{FE2} *	6	14			V _{CE} = 5.0 V, I _C = 1.0 A
Collector Saturation Voltage	V _{CE(sat)} *		0.35	1.0	V	I _C = 1.0 A, I _B = 0.2 A
Base Saturation Voltage	V _{BE(sat)} *		1.0	1.5	V	I _C = 1.0 A, I _B = 0.2 A
Gain Bandwidth Product	f _T		50		MHz	V _{CE} = 10 V, I _E = -100 mA
Output Capacitance	C _{ob}		20		pF	V _{CB} = 10 V, I _E = 0, f = 1.0 MHz
Turn-on Time	t _{on}		0.03	0.5	μs	I _C = 1.0 A, R _L = 150 Ω I _{B1} = -I _{B2} = 0.2 A
Storage Time	t _{stg}		1.5	2.0	μs	
Fall Time	t _f		0.1	0.7	μs	

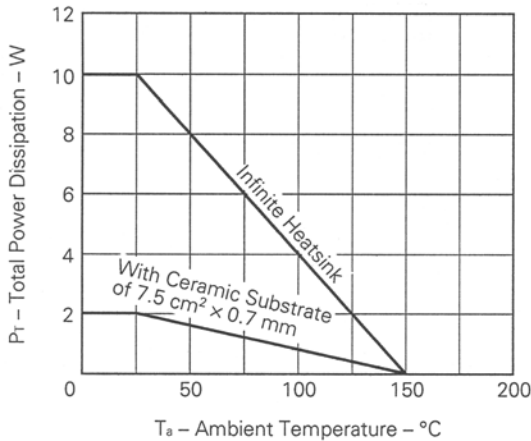
* Pulsed: PW ≤ 350 μs, Duty Cycle ≤ 2 %

h_{FE} Classification

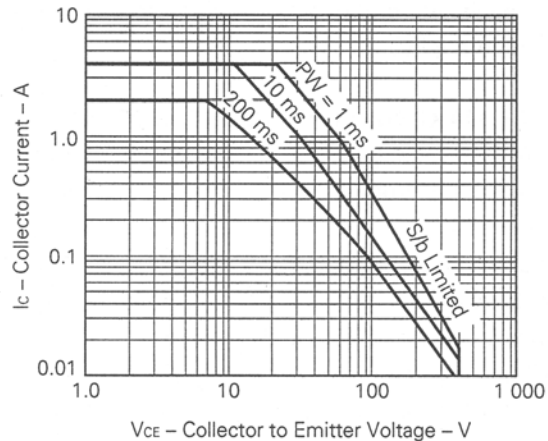
MARKING	L	K
h _{FE}	40 to 80	60 to 120

TYPICAL CHARACTERISTICS (T_a = 25 °C)

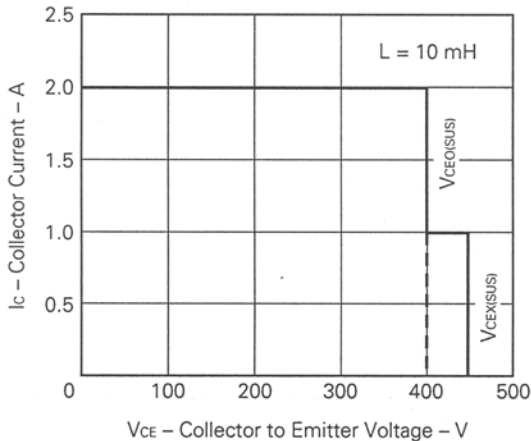
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



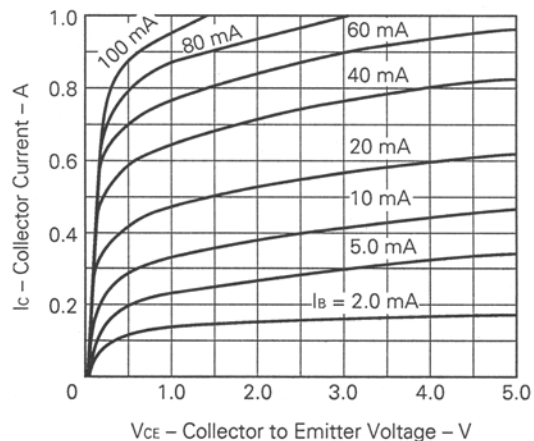
FORWARD BIAS SAFE OPERATING AREA



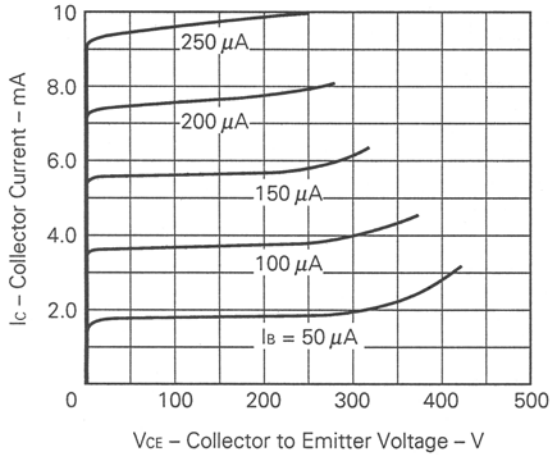
REVERSE BIAS SAFE OPERATING AREA



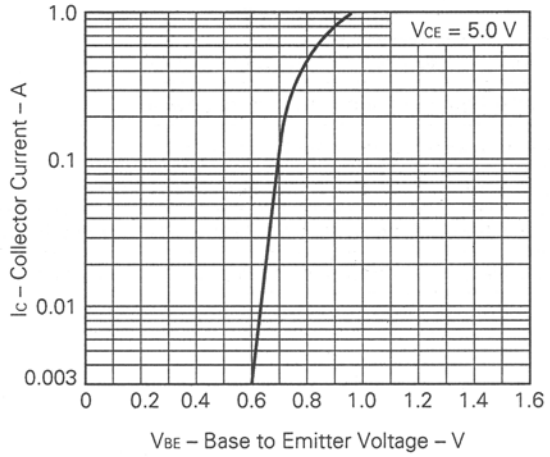
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



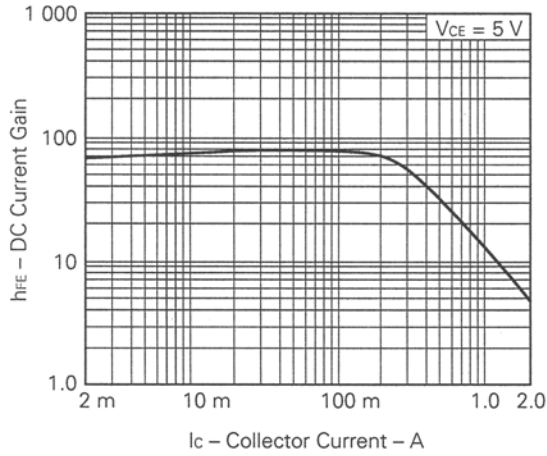
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



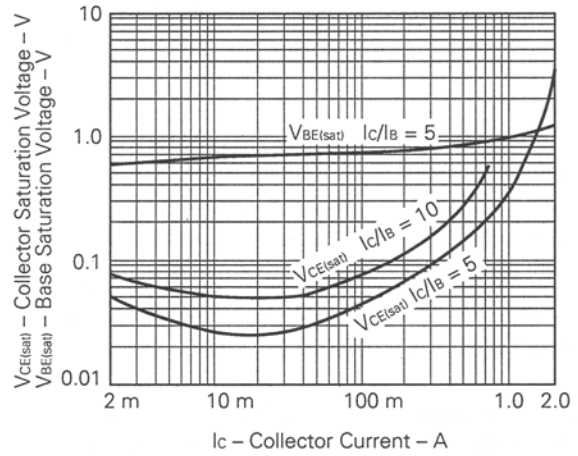
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



DC CURRENT GAIN vs. COLLECTOR CURRENT



COLLECTOR AND BASE SATURATION VOLTAGE vs. COLLECTOR CURRENT



TURN-OFF TIME vs. COLLECTOR CURRENT

